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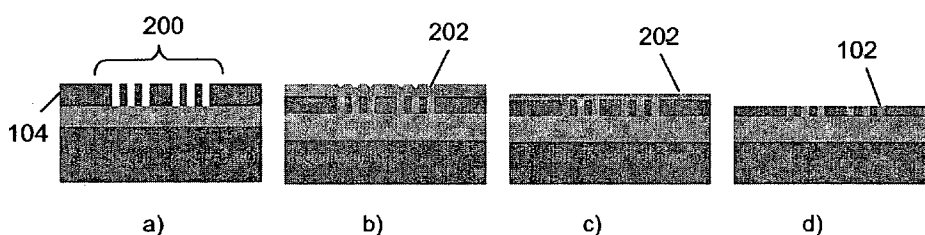


Figure 2

(57) Abstract: A method of forming a photonic crystal (PhC) structure and a PhC structure formed by such method. The method comprises forming holes in a Si-based host layer; filling the holes with a high-density plasma (HDP) deposited Si-based oxide and such that a surface of the Si-based host layer is directly covered with the Si-based oxide; performing at least a selective wet etching step for etching the Si-based oxide such that a surface of the resulting PhC structure is planarized.

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